



Application Specific Discretes
A.S.D.TM

ESDA25W

**DUAL TRANSILTM ARRAY
FOR ESD PROTECTION**

MAIN APPLICATIONS

Where transient overvoltage protection in ESD sensitive equipment is required, such as :

- Computers
- Printers
- Communication systems
- Wireline and wireless telephone sets.
- Set top boxes

FEATURES

- 2 unidirectional TRANSILTM functions.
- Breakdown voltage : $V_{BR} = 25V$ min.
- Low leakage current : $< 1\mu A$.
- Very low PCB space consuming : 4.2 mm^2 typically.

DESCRIPTION

The ESDA25W is a 2-bit wide monolithic suppressor designed to protect components which are connected to data and transmission lines against ESD.

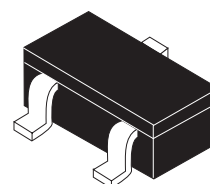
It clamps the voltage just above the logic level supply for positive transients, and to a diode drop below ground for negative transients.

BENEFITS

- High ESD protection level : up to 25 kV.
- High integration.
- Suitable for high density boards.

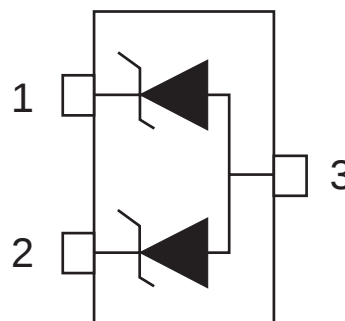
COMPLIES WITH THE FOLLOWING STANDARDS :

- IEC61000-4-2 level 4
- MIL STD 883C-Method 3015-6 : class 3.
(human body model)



SOT323-3L

FUNCTIONAL DIAGRAM



ESDA25W

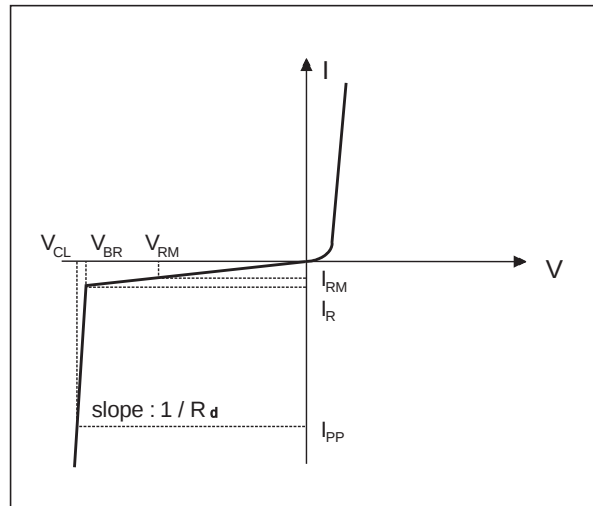
ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^{\circ}\text{C}$)

Symbol	Parameter	Test conditions	Value	Unit
V_{PP}	ESD discharge	MIL STD 883C - Method 3015-6 IEC61000-4-2, air discharge IEC61000-4-2, contact discharge	25 16 9	kV
P_{PP}	Peak pulse power (8/20 μs)		400	W
T_{op}	Operating temperature range	Note 1	- 40 to + 85	$^{\circ}\text{C}$
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature range		- 55 to + 150	$^{\circ}\text{C}$
T_L	Lead solder temperature (10 secondes duration)		260	$^{\circ}\text{C}$

Note 1: The evolution of the operating parameters versus temperature is given trough curves and αT parameter

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$)

Symbol	Parameter
V_{RM}	Stand-off voltage
V_{BR}	Breakdown voltage
V_{CL}	Clamping voltage
I_{RM}	Leakage current
I_{PP}	Peak pulse current
αT	Voltage temperature coefficient
C	Capacitance per line
R_d	Dynamic resistance
V_F	Forward voltage drop



Types	V_{BR} @ I_R		I_{RM} @ V_{RM}		R_d	αT	C	V_F @ I_F		
	min.	max.	max.		typ. note 2	max. note 3	typ. 0V bias	max.		
	V	V	mA	μA	V	Ω	$10^{-4} / ^\circ C$	pF	V	mA
ESDA25W	25	30	1	1	24	1.1	10	65	1.2	10

note 2 : Square pulse $I_{pp} = 15\text{A}$, $t_p = 2.5\mu\text{s}$.

note 3 : $\Delta V_{BR} = \alpha T * (T_{amb} - 25^{\circ}\text{C}) * V_{BR}(25^{\circ}\text{C})$

Fig. 1: Peak pulse power dissipation versus initial junction temperature

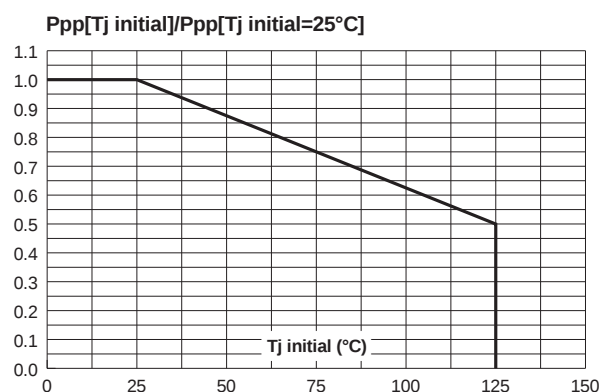


Fig. 2: Peak pulse power versus exponential pulse duration ($T_j \text{ initial} = 25^\circ\text{C}$)

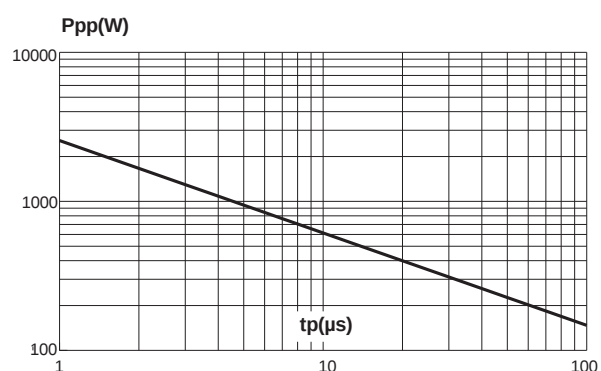


Fig. 3: Clamping voltage versus peak pulse current ($T_j \text{ initial} = 25^\circ\text{C}$). Rectangular waveform $t_p = 2.5 \mu\text{s}$.

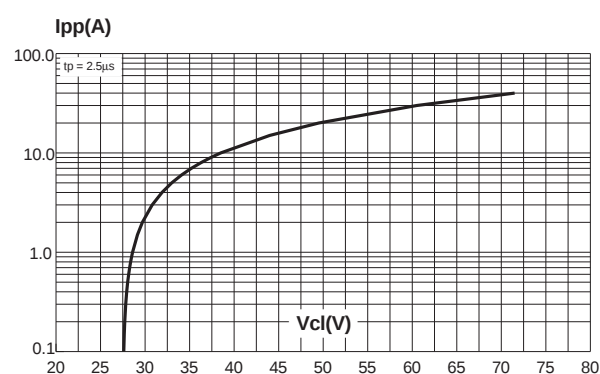


Fig. 4: Capacitance versus reverse applied voltage (typical values).

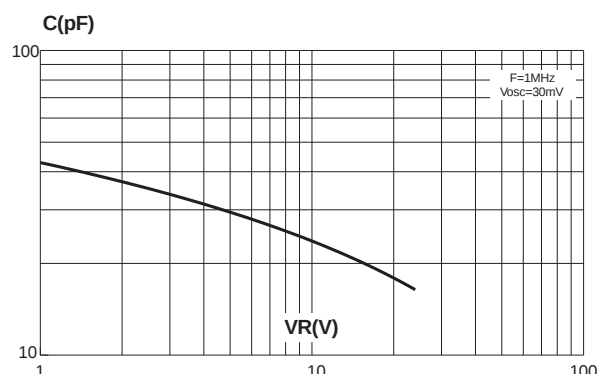


Fig. 5: Relative variation of leakage current versus junction temperature (typical values).

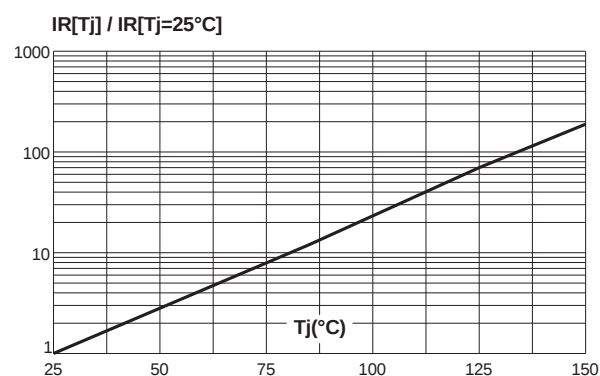
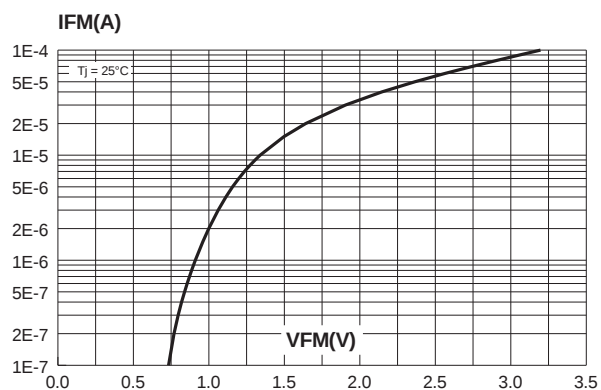
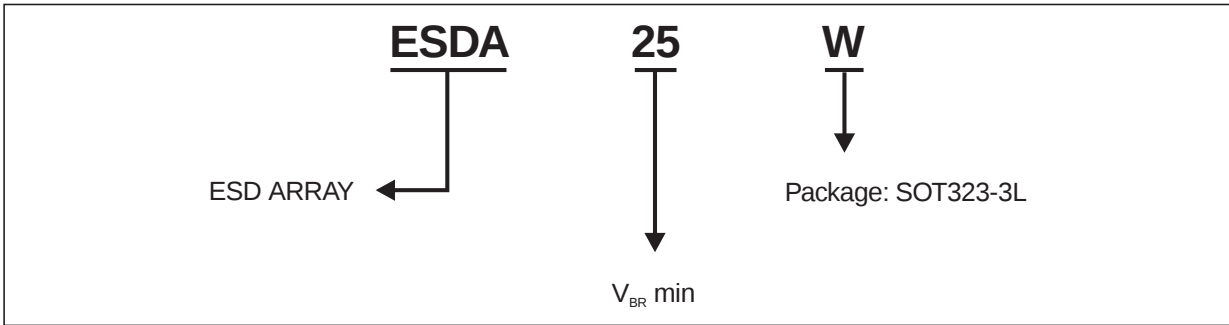


Fig. 6: Peak forward voltage drop versus peak forward current (typical values).



ESDA25W

ORDER CODE



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
ESDA25W	E25	SOT323-3L	5.4 mg.	3000	Tape & reel

PACKAGE MECHANICAL DATA
SOT323-3L

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.8		1.1	0.031		0.043
A1	0.0		0.1	0.0		0.004
b	0.25		0.4	0.010		0.016
c	0.1		0.26	0.004		0.010
D	1.8	2.0	2.2	0.071	0.079	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e		0.65			0.026	
H	1.8	2.1	2.4	0.071	0.083	0.094
L	0.1	0.2	0.3	0.004	0.008	0.012
θ	0		30°	0		30°

Mechanical specifications	
Lead plating	Tin-lead
Lead plating thickness	5µm min. 25 µm max.
Lead material	Sn / Pb (70% to 90% Sn)
Body material	Molded epoxy
Epoxy meets	UL94,V0

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